

a plurality of bonding wires for connecting said plural bonding pads to each other,

wherein said second semiconductor chip is mounted on said wiring layer by an adhesive material and said wiring layer is provided on said first semiconductor chip without using an adhesive material.--

--8. (amended) The semiconductor device according to claim 7, wherein,

B' a first bonding wire connects one of said plural bonding pads on said substrate to one of said plural bonding pads on said first semiconductor chip;

a second bonding wire connects one of said plural bonding pads on said substrate to one of said plural bonding pads on said wiring layer; and

a third bonding wire connects said one of said plural bonding pads on said wiring layer to one of said plural bonding pads on said semiconductor substrate.--

B2 pub. 12. (amended) A semiconductor device comprising:

a substrate;

a first semiconductor chip on said substrate;

a second semiconductor chip overlying said first semiconductor chip;

a wiring layer between said first and second

B2 semiconductor chips, said wiring layer including a conductor within said wiring layer;

a plurality of bonding pads on said wiring layer, said substrate and said first and second semiconductor chips; and

a plurality of bonding wires for connecting said plural bonding pads to each other,

wherein said second semiconductor chip is mounted on said wiring layer by an adhesive material and said wiring layer is provided on said first semiconductor chip without using an adhesive material.--

B3 pulci → --14. (amended) The semiconductor device according to claim 12, wherein

a first bonding wire connects one of said plural bonding pads on said substrate to one of said plural bonding pads on said first semiconductor chip;

a second bonding wire connects one of said plural bonding pads on said substrate to one of said plural bonding pads on said wiring layer; and

a third bonding wire connects another one of said plural bonding pads on said wiring layer to one of said plural bonding pads on said semiconductor substrate,

said second and third bonding wire being electrically connected through said conductor.--

*rule 1*  
*B4*

--17. (amended) A semiconductor device comprising:  
a substrate;  
a first semiconductor chip on said substrate;  
a second semiconductor chip overlying said first semiconductor chip;  
a wiring layer between said first and second semiconductor chips, said wiring layer including a conductor traversing said wiring layer;  
a plurality of bonding pads on said wiring layer, said substrate and said first and second semiconductor chips; and  
a plurality of bonding wires for connecting said plural bonding pads to each other,  
wherein said second semiconductor chip is mounted on said wiring layer by an adhesive material and said wiring layer is provided on said first semiconductor chip without using an adhesive material.--

*B5 sub c1*

--20. (amended) A semiconductor device comprising:  
a substrate;  
a first semiconductor chip on said substrate;  
a second semiconductor chip overlying said first semiconductor chip;  
a wiring layer between said first and second semiconductor chips, said wiring layer including a polyimide tape having a copper foil layer therein;